



2SA1965-S — PNP Epitaxial Planar Silicon Transistor

Muting Circuit Applications

Features

- Ultrasmall-sized package permitting applied sets to be made small and slim.
- Small output capacitance.
- Low collector-to-emitter saturation voltage.
- Low ON resistance.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V _{CB0}		-15	V
Collector-to-Emitter Voltage	V _{CEO}		-10	V
Emitter-to-Base Voltage	V _{EBO}		-5	V
Collector Current	I _C		-100	mA
Collector Current (Pulse)	I _{CP}		-200	mA
Base Current	I _B		-20	mA
Collector Dissipation	P _C		150	mW
Junction Temperature	T _J		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I _{CBO}	V _{CB} =-12V, I _E =0A			-0.1	μA
Emitter Cutoff Current	I _{EBO}	V _{EB} =-4V, I _C =0A			-0.1	μA
DC Current Gain	h _{FE}	V _{CE} =-2V, I _C =-5mA	200		600	
Gain-Bandwidth Product	f _T	V _{CE} =-5V, I _C =-10mA		600		MHz
Output Capacitance	C _{ob}	V _{CB} =-10V, f=1MHz		5.0		pF

Marking : KA

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SANYO Semiconductor Co., Ltd.

TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

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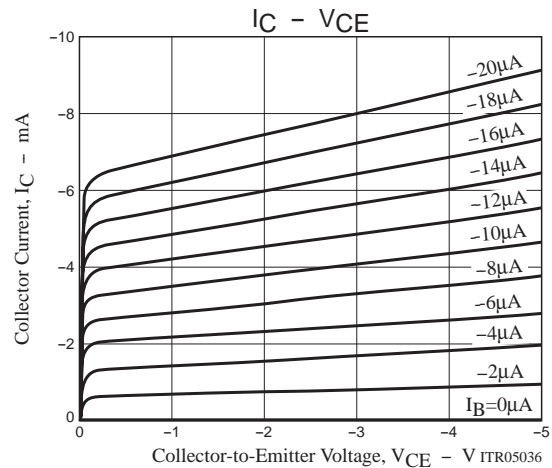
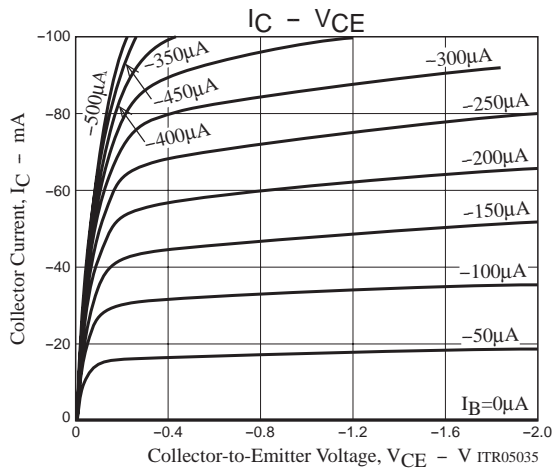
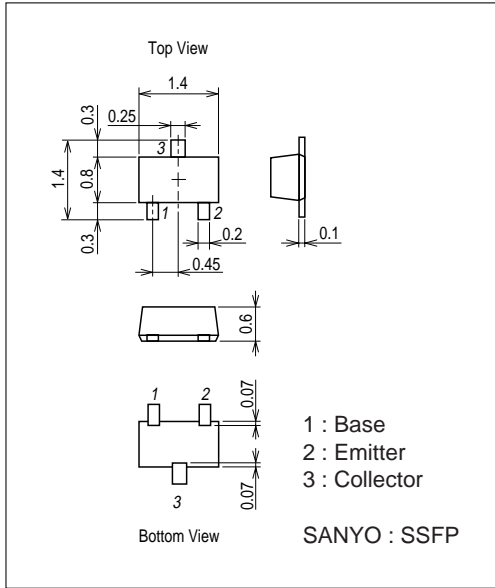
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -10\text{mA}$, $I_B = -1\text{mA}$		-16	-35	mV
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = -10\text{mA}$, $I_B = -1\text{mA}$		-0.75	-1.1	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -10\mu\text{A}$, $I_E = 0\text{A}$	-15			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}$, $R_{BE} = \infty$	-10			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -10\mu\text{A}$, $I_C = 0\text{A}$	-5			V
On Resistance	R_{on}	$I_B = -3\text{mA}$, $f = 1\text{MHz}$		1.2		Ω

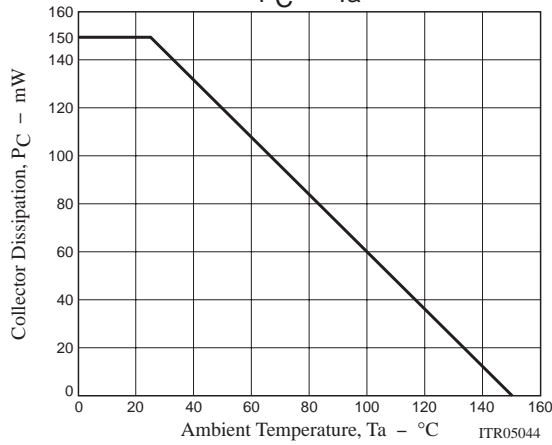
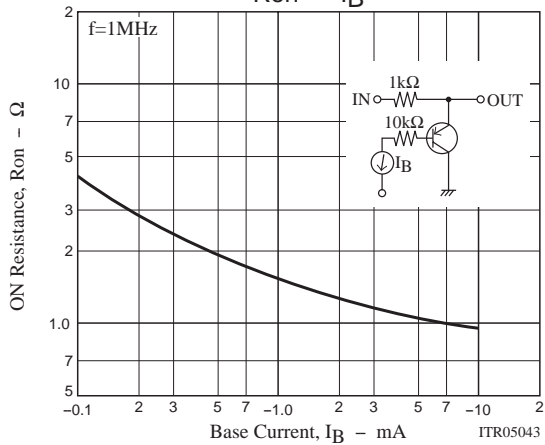
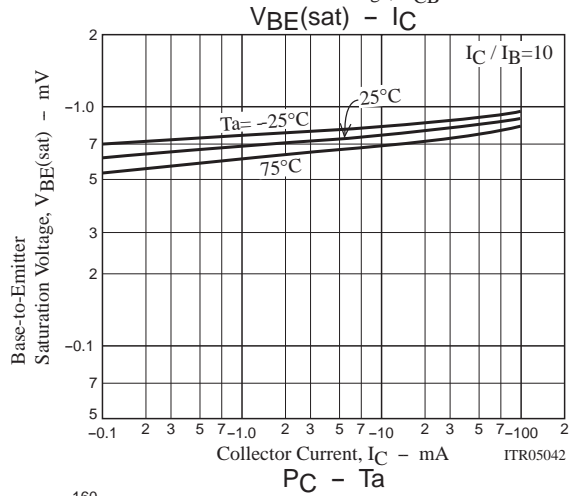
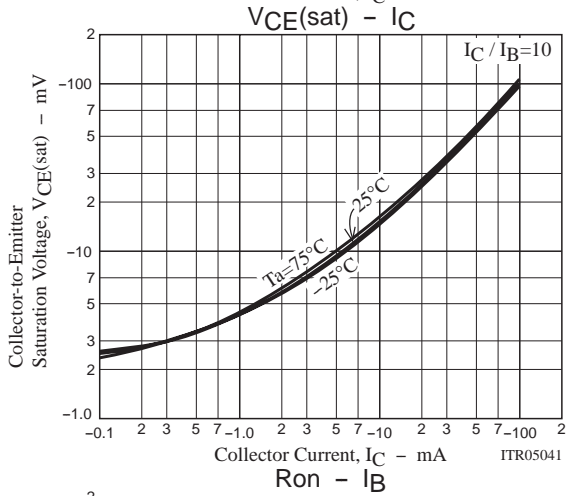
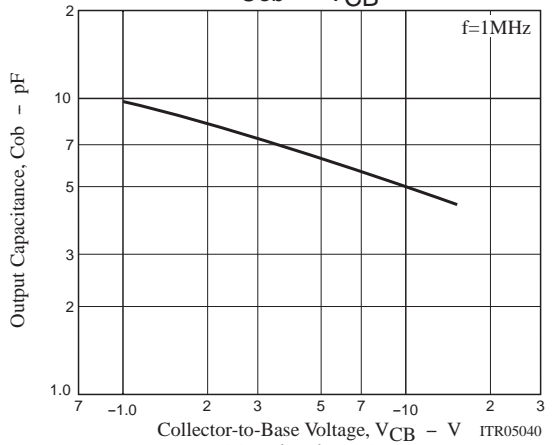
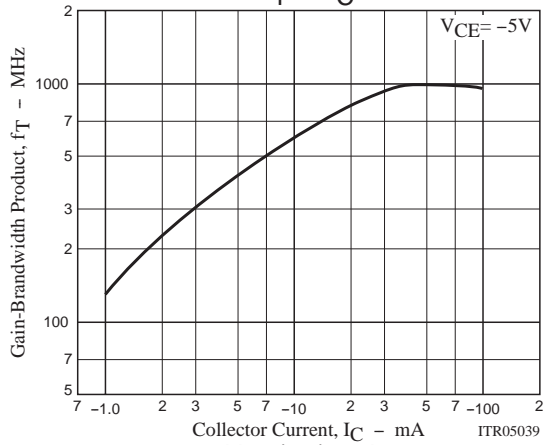
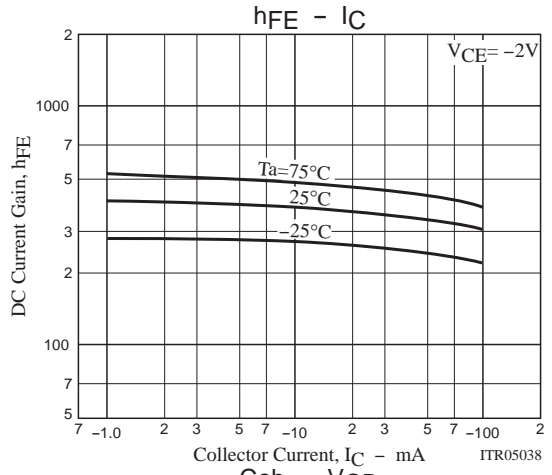
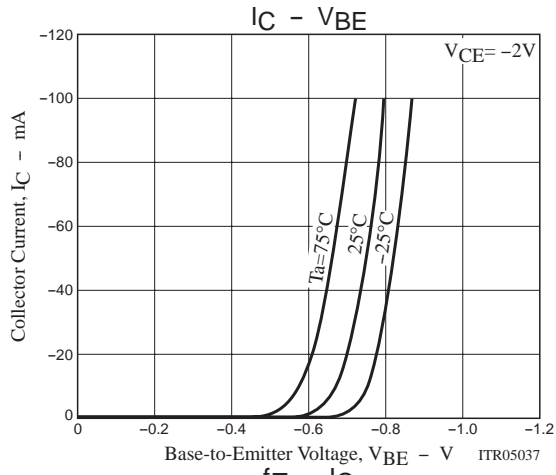
Package Dimensions

unit : mm (typ)

7029-002



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